

b2 10. (Amended) A method according to claim 8, wherein the halogen is [fluorine or] chlorine.

b3 13. (Amended) A method of fabricating a thin film transistor, said method comprising the steps of:

forming a crystalline semiconductor island formed over a glass substrate:

forming a silicon oxide film formed [to cover] over the crystalline semiconductor island;

and

forming a conductive film including at least one aluminum, titanium, and titanium nitride, said conductive film being formed on the silicon oxide film,

wherein the silicon oxide film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$ or less and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

14. (Amended) A method according to claim 13, wherein the halogen is [fluorine or] chlorine.

b4 18. (Amended) A method according to claim 17, wherein the halogen is [fluorine or] chlorine.

Please add new claims 21 through 29 as follows:

b5 --21. A method according to claim 1, wherein the halogen is fluorine.

22. A method according to claim 8, wherein the halogen is fluorine.

23. A method according to claim 13, wherein the halogen is fluorine.

24. A method according to claim 17, wherein the halogen is fluorine.

25. A method of fabricating a thin film transistor, said method comprising the steps of:

forming at least a thin film transistor including a crystalline semiconductor island, a gate electrode adjacent to the crystalline semiconductor island with a gate insulating film interposed therebetween;

forming an interlayer insulating film comprising silicon oxide over the thin film transistor,

wherein the interlayer insulating film includes halogen at a concentration of $5 \times 10^{20} \text{ cm}^{-3}$ or less and carbon at a concentration of $5 \times 10^{19} \text{ cm}^{-3}$ or less.

26. A method according to claim 25, wherein the halogen is chlorine.

27. A method according to claim 25, wherein the halogen is fluorine.